

LDMOS Die Technology



Infineon introduces the next generation of its GOLDMOS[®] LDMOS (laterally diffused metal-oxide semiconductor) die technology for RF transistors. In addition to linear efficiency, ultra-wide-bandwidth performance, and reduced memory effect, the transistors will provide good thermal performance. The transistors will be integrated into products designed for use in UMTS/WCDMA, GSM, CDMA, EDGE, TDSCDMA, PCS/DCS, MMDS, TV broadcast, and DAB amplifiers. For example, one of the products incorporating the technology is the single-ended, 100 watt PTFA211001E 2.1 GHz device. In 2-carrier WCDMA 3GPP mode, this device has an average output of 22 watts and 16.5 dB gain with 30 percent efficiency. It has an ultra-wide-bandwidth of several hundred MHz, third-order intermodulation distortion (IM3) performance of -150.37 dBc, and a thermal resistance of 0.38×10^6 C/W.

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